EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	93	measur$3 and polycrystalline adj wafer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:04
L2	63	photovoltaic adj devices and (slicing or dice$3 or diced)and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:05
L3	0	defect adj characteriz$3 and classificat$3 and crystal adj growth and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:07
L4	54	defect and classificat$3 and crystal adj growth and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:08
L5	0	(defects or grain adj boundaries)and processing adj wafer$1 and classificat$3 and crystal adj growth and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:09
L6	75	(defects or grain adj boundaries)and processing adj wafer$1 and crystal adj growth and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:10
L7	3	L1 and L2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:10
L8	0	L6 and L7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:11
L9	0	L7 and(defects or grain adj boundaries)and crystal adj growth and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:11

L10	0	L7 and(defects or grain adj boundaries)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:12
L11	0	L7 and defects and crystal adj growth and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:12
L12	10	L2 and(imaging or ccd or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:15
L13	3	L12 and @ad< "20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:16
L14	0	L2 and inspect$3 adj defects and crystal adj growth and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:29
L15	0	L2 and inspect$3 and defects and crystal adj growth and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:29
L16	4	L2 and inspect$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:30
L17	1	L16 and(defects or grain adj boundaries)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:30
L18	0	L17 and @ad< "20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:30
L19	55	L2 and(defects or variances or voids or defects or stacking adj faults or inclusions or impurities or grain or crystal adj boundaries)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:35
L20	1	L19 and(imaging or ccd or camera or CMOS or IR)and surface adj wafer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:35

L21	0	L20 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:36
L22	55	L2 and L19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:36
L23	20	L22 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:36
L24	13	L23 and(compar$3 or match$3) and(wafer or ingot or cells or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:44
L25	11	L23 and(compar$3 or match$3) same(wafer or ingot or cells or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:46
L26	11	L25 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:46
L27	0	L23 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:49
L28	0	L23 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar$3 or match $3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:50
L29	0	L19 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar$3 or match $3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:50
L30	0	L2 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar$3 or match $3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:51
L31	0	L2 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar$3 or match $3)and surface adj wafer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:51

L32	0	L1 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar$3 or match $3)and surface adj wafer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:52
L33	0	L6 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar$3 or match $3)and surface adj wafer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:52
L34	0	L2 and(imaging or ccd or camera or CMOS or IR)and (compar$3 or match$3)and surface adj wafer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:53
L35	5	(imaging or ccd or camera or CMOS or IR)and(compar$3 or match$3)and photovoltaic adj devices and(slicing or dice$3 or diced)and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:54
L36	2	L35 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:54
L37	2	L36 and(defects or variances or voids or defects or stacking adj faults or inclusions or impurities or grain or crystal adj boundaries)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:55
L38	4	L2 and(wafer$1 or semiconductor$1 or IC or intergrated adj circuit) and inspect$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:04
L39	10	L1 and(wafer$1 or semiconductor$1 or IC or intergrated adj circuit) and inspect$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:04
L40	0	L38 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar$3 or match $3)and surface adj wafer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:04
L41	0	L38 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar$3 or match $3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:05
L42	0	L39 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar$3 or match $3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:05

L43	0	L39 and(imaging or ccd or camera or CMOS or IR)and (compar$3 or match$3)and photovoltaic adj devices and (slicing or dice$3 or diced)and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:05
L44	0	L39 and(imaging or ccd or camera or CMOS or IR)and (compar$3 or match$3)and (cell adj solar or cell or memory or wafer$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:06
L45	4	L39 and(imaging or ccd or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:06
L46	4	L45 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:06
L47	1	L46 and(defects or variances or voids or defects or stacking adj faults or inclusions or impurities or grain or crystal adj boundaries)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:07
L48	0	L1 and produc$4 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:16
L49	0	L2 and produc$4 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:16
L50	0	L4 and produc$4 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:16
L51	0	L4 and(produc$4 or obtaining) and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:16
L52	0	L39 and(produc$4 or obtaining) and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:17
L53	0	L35 and(produc$4 or obtaining) and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:17

L54	0	L37 and(produc$4 or obtaining) and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:17
L55	1	crystallographic adj structure and(produc$4 or obtaining)and wafer adj image and cell adj image and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:18
L56	1	crystallographic adj structure and(produc$4 or obtaining)and wafer adj image and(cell adj image or cells or cell or wafer or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:20
L57	3130	crystallographic adj structure and(produc$4 or obtaining)and (cell adj image or cells or cell or wafer or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:20
L58	2	L57 and photovoltaic adj devices and(slicing or dice$3 or diced)and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:21
L59	2	L58 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:21
S1	2124	sheela chawan.Xa.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:40
S2	2338	sheela chawan.Xp.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:46
S3	2	S1 and wafer adj polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:46
S4	2	S2 and wafer adj polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:47
S5	22	S1 and wafer adj inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:48

S6	22	S2 and wafer adj inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:48
S7	156	wafer adj pad and inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 16:05
S8	156	wafer adj pad and inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:04
S9	27	S8 and notch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:04
S10	337122	crystallographic asj structure and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:09
S11	966	crystallographic adj structure and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:09
S12	191	crystallographic adj structure same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:09
S13	150	S12 and (@ad<"20040202" or @rlad<"20040202" or @prad<"20040202" or @ptad<"20040202")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:21
S14	117	S12 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:21
S15	16	S14 and(solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:22
S16	16	S15 and (compar$3 or match$3)and wafer and(solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:23

S17	41	crystallographic adj structure and wafer and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:39
S18	5	S17 and(compar$3 or match$3) and wafer and(solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:40
S19	4	S18 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:40
S20	110	((("(4352948") or ("6161054") or ("5203005") or ("5287472") or ("5292677") or ("5485097") or ("6243308") or ("4435498") or ("4471483") or ("4493055") or ("4519035") or ("4543444") or ("4898835") or ("4999689") or ("5019736") or ("5024972") or ("5252507") or ("5265847") or ("5315130") or ("5362666") or ("5393617") or ("5478363") or ("5491665") or ("5536964") or ("5552243") or ("5619419") or ("5624771") or ("5656392") or ("5657284") or ("5698453") or ("5698342") or ("5716459") or ("5808947") or ("5821160") or ("5851693") or ("5926419") or ("6040912") or ("RE36644") or ("6046078") or ("6140140") or ("6161213") or ("6225167") or ("6330819") or ("4304641") or ("4338480") or ("4353160") or ("4385198") or ("4400221") or ("4400868") or (").pn.")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/10 16:43
S21	106	S20 and(@ad<"20040202" or @rlad<"20040202" or @prad<"20040202" or @ptad<"20040202")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:43
S22	106	S20 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:43
S23	0	S22 and crystallographic adj structure and wafer and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:44

S24	0	S22 and crystallographic adj structure and wafer and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:46
S25	5	S22 and inspect$3 and (crystallographic adj structure or wafer or ingot or cells or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:05
S26	4	S25 and(compar$3 or match$3) and(solar adj cell or cell crystallographic adj structure or wafer or ingot or cells or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:06
S27	4	S26 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:07
S28	4742	crystallographic adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:10
S29	4328355	(wafer$1 or semiconductor or solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:11
S30	98638	S29 and inspect$3 and(cells or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:20
S31	153527	S29 and inspect$3 and(cells or cell or wafer or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:21
S32	4742	crystallographic adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:22
S33	632	S31 and S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:27
S34	1	S33 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:28

S35	3	inspect$3 and solar adj cell and matrix and convert$3 and electricity and solar adj cell and treating and silicon adj wafers and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:32
S36	2	S35 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:33
S37	1	S35 and (compar$3 or match$3)and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:39
S38	1	S32 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:40
S39	17	S29 and (compar$3 or match$3)and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:40
S40	3	S39 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:41
S41	1	S39 and crystallographic adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:51
S42	1	S39 and crystallographic adj structure and wafer adj structure and manufactured adj cell and crystallographic adj image and information and sufficient adj establish and correspondence and cell and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:58
S43	1	S39 and crystallographic adj structure and wafer adj structure and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:59
S44	1	crystallographic adj structure and wafer adj structure and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:59

S45	2	S29 and crystallographic adj structure and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:00
S46	0	S45 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:01
S47	1	S32 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:04
S48	607	S32 and inspect$3 and(cells or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:06
S49	1	S48 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:06
S50	587	S48 and(compar$3 or match$3) and (memory or cell or memory adj cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:07
S51	1	S48 and(compar$3 or match$3) same(memory or cell or memory adj cell)same wafer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:08
S52	1	S50 and crystallographic adj structure and wafer adj structure and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:09
S53	1	S50 and wafer adj structure and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:09
S54	1	S50 and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:10
S55	297	S50 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:10

S56	12	S55 and(compar$3 or match$3) and wafer and(solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:11
S57	13	S55 and inspect$3 and wafer$1 and(cells or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:12
S58	0	S55 and inspect$3 adj wafer$1 same(cells or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:13
S59	0	S55 and inspect$3 adj wafer$1 and(cells or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:13
S60	3559	S28 and(wafer$1 or semiconductor or solar adj cell or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:14
S61	2	S60 and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:14
S62	0	S61 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:14
S63	2	S32 and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:15
S64	1818	S32 and(wafer$1 or semiconductor or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:16
S65	237	S32 and(wafer$1 or semiconductor or memory)and inspect$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:16
S66	119	S65 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:16

S67	12	S66 and(compar$3 or match$3) and wafer and(solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:19
S68	38	S32 and inspect$3 and(compar $3 or match$3)and wafer and (solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:28
S69	41	S32 and inspect$3 and(compar $3 or match$3)and wafer and (solar adj cell or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:29
S70	13	S69 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:29
S71	85837	analyz$3 and(crystalline or crystallographic adj structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:35
S72	18	S71 and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:36
S73	1	S72 and(wafer$1 or semiconductor or memory)and inspect$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:36
S74	1	inspect$3 and photovoltaic adj area and manufactured and crystalline adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:43
S75	0	S74 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:44
S76	0	S72 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:46
S77	0	S71 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:47

S78	31037	S71 and(imaging or ccd or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:47
S79	8	S78 and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:47
S80	2	S79 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:48
S81	2106	S78 and(wafer$1 or semiconductor$1 or IC or intergrated adj circuit) and inspect$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:51
S82	45	S81 and(compar$3 or match$3) same(memory or cell or memory adj cell)same wafer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:52
S83	18	S82 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:52
S84	25	S17 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 19:17
S85	5	S72 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 19:48
S86	118795	(wafer$1 or semiconductor$1 or IC or intergrated adj circuit) and inspect$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 19:49
S87	9	S86 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 19:49
S88	1	S87 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 19:49

S89	533	crystallographic adj structure and(wafer or ingot)and section	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:15
S90	161	S89 and analyz$3 and (crystalline or crystallographic adj structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:16
S91	0	S89 and analyz$3 and (crystalline or crystallographic adj structure) same ignot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:16
S92	0	S90 and(imaging or ccd or camera or CMOS or IR)and wafer adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:17
S93	120	S90 and(imaging or ccd or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:17
S94	48	S93 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:22
S95	0	S93 and etching and texturisation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:59
S96	7	(wafer$1 or semiconductor$1 or IC or intergrated adj circuit) and etching and texturisation and inspect$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:00
S97	2	S96 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:00
S98	0	S97 and(compar$3 or match$3) same(memory or cell or memory adj cell or die)same wafer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:01
S99	0	S97 and(compar$3 or match$3) and(memory or cell or memory adj cell or die)and wafer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:01

S100	2	S97 and(memory or cell or memory adj cell or die)and wafer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:01
S101	161	S89 and S90	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:05
S102	0	S101 and(wafer$1 or semiconductor$1 or IC or intergrated adj circuit)and etching and texturisation and inspect$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:06
S103	0	S101 and etching and texturisation and inspect$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:06
S104	0	S101 and etching and texturisation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:07
S105	1	S89 and etching and texturisation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:07
S106	20	S89 and solar adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:08
S107	8	S106 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:08
S108	2468	ingot and production adj process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:10
S109	523	S108 and wafer$3 and production adj process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:11
S110	128	S109 and cell and production adj process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:11

S111	1	S110 and wafer adj position$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:12
S112	75	S110 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:13
S113	0	S112 and cell adj inspect$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:13
S114	75	S112 and(memory or cell or memory adj cell or die)and wafer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:14
S115	0	S114 and(imaging or ccd or camera or CMOS or IR)and wafer adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:14
S116	12	S114 and(imaging or ccd or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:14
S117	10	S116 and(compar$3 or match $3)and(memory or cell or memory adj cell or die)and wafer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:15
S118	10	S117 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:15

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